

LET20045C

RF power transistor from the LdmoST family of n-channel enhancement-mode lateral MOSFETs

Features

- Excellent thermal stability
- Common source configuration
- P_{OUT} (@ 28 V)= 54 W with 13.3 dB gain @ 2000 MHz
- P_{OUT} (@ 36 V)= 65 W with 12.5 dB gain @ 2000 MHz
- BeO free package
- In compliance with the 2002/95/EC European directive

Description

The LET20045C is a common source n-channel enhancement-mode lateral field-effect RF power transistor designed for broadband commercial and industrial applications at frequencies up to 2.0 GHz. The LET20045C is designed for high gain and broadband performance operating in common source mode at 36 V. It is ideal for base station applications requiring high linearity.

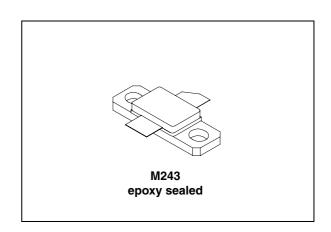


Figure 1. Pin out

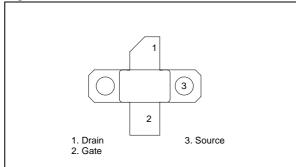


Table 1. Device summary

Order code	Package	Branding
LET20045C	M243	LET20045C

Maximum ratings LET20045C

1 Maximum ratings

Table 2. Absolute maximum ratings ($T_{CASE} = 25 \, ^{\circ}C$)

Symbol	Parameter	Value	Unit
V _{(BR)DSS}	Drain-source voltage	80	V
V_{GS}	Gate-source voltage	-0.5 to +15	V
I _D	Drain current	12	Α
P _{DISS}	Power dissipation (@ T _C = 70 °C)	130	W
TJ	Max. operating junction temperature	200	°C
T _{STG}	T _{STG} Storage temperature		°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{th(JC)}	Junction-case thermal resistance	1.0	°C/W

2 Electrical characteristics

 $T_C = 25$ °C

Table 4. Static

Symbol	Test conditions		Тур.	Max.	Unit
V _{(BR)DSS}	$V_{GS} = 0 \text{ V}; I_{DS} = 10 \text{ mA}$	80			V
I _{DSS}	V _{GS} = 0 V; V _{DS} = 28 V			1	μΑ
I _{GSS}	$V_{GS} = 5 \text{ V}; V_{DS} = 0 \text{ V}$			1	μΑ
V _{GS(Q)}	$V_{DS} = 28 \text{ V}; I_D = 100 \text{ mA}$	2.0		5.0	V
V _{DS(ON)}	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}$		0.8	1.2	V
G _{FS}	$V_{DS} = 10 \text{ V}; I_D = 3 \text{ A}$	2.5			mho
C _{ISS}	V _{GS} = 0 V; V _{DS} = 28 V; f = 1 MHz		77		pF
C _{OSS}	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}; f = 1 \text{ MHz}$		39		pF
C _{RSS}	V _{GS} = 0 V; V _{DS} = 28 V; f = 1 MHz		1.2		pF

Table 5. Dynamic

Symbol	Test conditions		Тур.	Max.	Unit
P _{OUT}	$V_{DD} = 28 \text{ V}; I_{DQ} = 500 \text{ mA}; P_{IN} = 2.5 \text{ W}; f = 2000 \text{ MHz}$	45	54	-	W
G _{PS}	$V_{DD} = 28 \text{ V}; I_{DQ} = 500 \text{ mA}; P_{IN} = 2.5 \text{ W}; f = 2000 \text{ MHz}$		13.3	-	dB
h _D	$V_{DD} = 28 \text{ V}; I_{DQ} = 500 \text{ mA}; P_{IN} = 2.5 \text{ W}; f = 2000 \text{ MHz}$		51	-	%
Load mismatch	V_{DD} = 28 V; I_{DQ} = 500 mA; P_{IN} = 2.5 W; f = 2000 MHz All phase angles	10:1			VSWR

Impedance data LET20045C

3 Impedance data

Figure 2. Impedance data

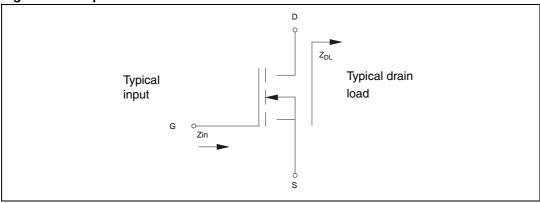


Table 6. Impedance data

Frequency	Z _{IN} (Ω)	Z _{DL} (Ω)
TBD	TBD	TBD

4 Typical performances

Figure 3. Gain vs output power and bias current

Figure 4. Gain and efficiency vs output power

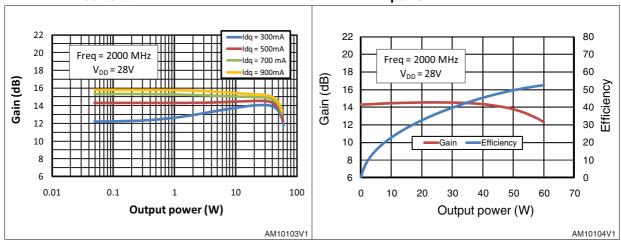


Figure 5. Gain vs output power and supply voltage

Figure 6. Efficiency vs output power and supply voltage

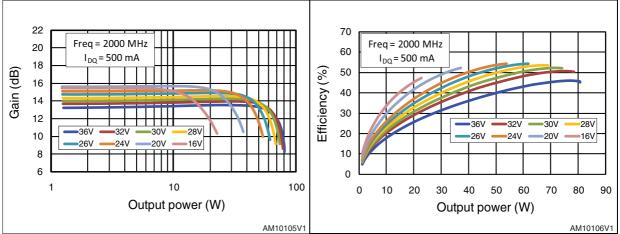


Figure 7. IMD vs output power @ 28 V

Figure 8. IMD vs output power @ 32 V

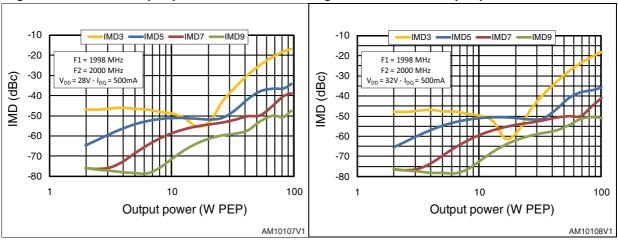
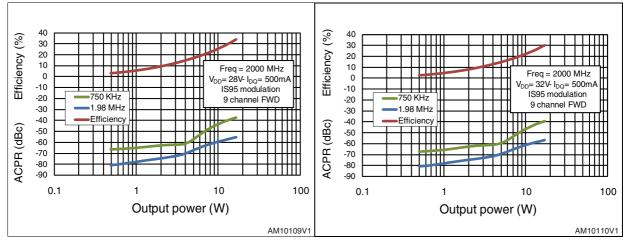


Figure 9. ACPR and efficiency vs output power @ 28 V

Figure 10. ACPR and efficiency vs output power @ 32 V



5 Package mechanical data

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Dim.	mm			inch		
Dim.	Min.	Тур	Max.	Min.	Тур	Max.
Α	5.21		5.72	0.205		0.225
В	5.46		6.48	0.215		0.255
С	5.59		6.1	0.22		0.24
D		14.27			0.562	
E	20.07		20.57	0.79		0.81
F	8.89		9.4	0.35		0.37
G	0.1		0.15	0.004		0.006
Н	3.18		4.45	0.125		0.175
I	1.83		2.24	0.072		0.088

1.78

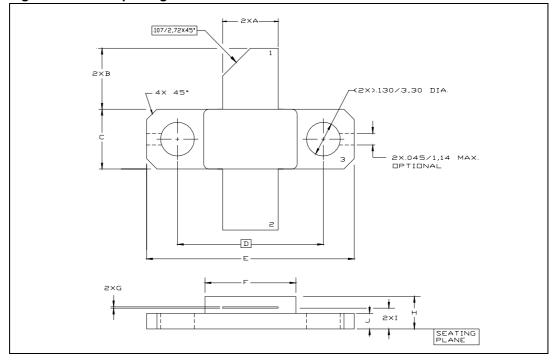
0.05

Table 7. M243 (.230 x .360 2L N/HERM W/FLG) mechanical data



1.27

J



0.07

Revision history LET20045C

6 Revision history

Table 8. Document revision history

Date	Revision	Changes
19-Jul-2011	1	Initial release.

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